

TOSHIBA Field Effect Transistor Silicon N-Channel MOS Type (U-MOSVI-H)

TPCA8039-H

High-Efficiency DC-DC Converter Applications
 Notebook PC Applications
 Portable Equipment Applications

- Small footprint due to a small and thin package
- High-speed switching
- Small gate charge: $Q_{sw} = 8.6 \text{ nC (typ.)}$
- Low drain-source ON-resistance: $R_{DS(ON)} = 3.8 \text{ m}\Omega \text{ (typ.)}$
- High forward transfer admittance: $|Y_{fs}| = 99 \text{ S (typ.)}$
- Low leakage current: $I_{DSS} = 10 \text{ }\mu\text{A (max) (}V_{DS} = 30 \text{ V)}$
- Enhancement mode: $V_{th} = 1.3 \text{ to } 2.3 \text{ V (}V_{DS} = 10 \text{ V, } I_D = 0.5 \text{ mA)}$

Absolute Maximum Ratings (Ta = 25°C)

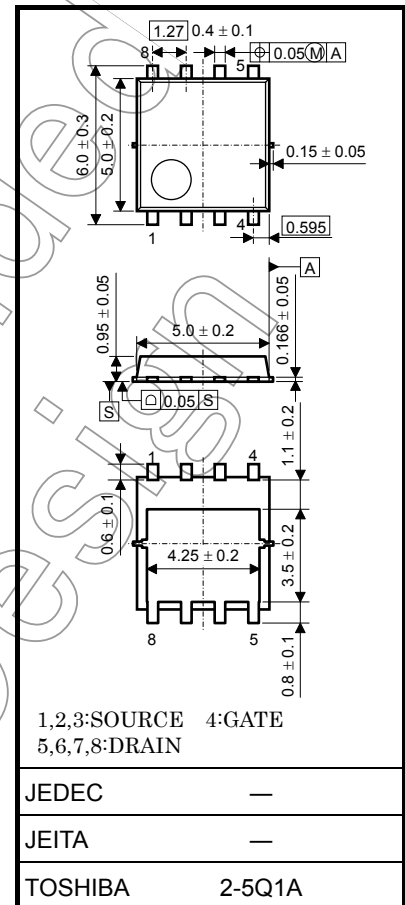
| Characteristic | | Symbol | Rating | Unit |
|---|-----------------|-----------|------------|------------------|
| Drain-source voltage | | V_{DSS} | 30 | V |
| Drain-gate voltage ($R_{GS} = 20 \text{ k}\Omega$) | | V_{DGR} | 30 | V |
| Gate-source voltage | | V_{GSS} | ± 20 | V |
| Drain current | DC (Note 1) | I_D | 34 | A |
| | Pulsed (Note 1) | I_{DP} | 102 | |
| Drain power dissipation ($T_c = 25^\circ\text{C}$) | | P_D | 45 | W |
| Drain power dissipation ($t = 10 \text{ s}$) (Note 2a) | | P_D | 2.8 | W |
| Drain power dissipation ($t = 10 \text{ s}$) (Note 2b) | | P_D | 1.6 | W |
| Single-pulse avalanche energy (Note 3) | | E_{AS} | 150 | mJ |
| Avalanche current | | I_{AR} | 34 | A |
| Repetitive avalanche energy ($T_c = 25^\circ\text{C}$) (Note 4) | | E_{AR} | 0.19 | mJ |
| Channel temperature | | T_{ch} | 150 | $^\circ\text{C}$ |
| Storage temperature range | | T_{stg} | -55 to 150 | $^\circ\text{C}$ |

Note: For Notes 1 to 4, refer to the next page.

Using continuously under heavy loads (e.g. the application of high temperature/current/voltage and the significant change in temperature, etc.) may cause this product to decrease in the reliability significantly even if the operating conditions (i.e. operating temperature/current/voltage, etc.) are within the absolute maximum ratings. Please design the appropriate reliability upon reviewing the Toshiba Semiconductor Reliability Handbook ("Handling Precautions"/"Derating Concept and Methods") and individual reliability data (i.e. reliability test report and estimated failure rate, etc).

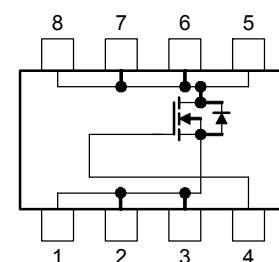
This transistor is an electrostatic-sensitive device. Handle with care.

Unit: mm



Weight: 0.069 g (typ.)

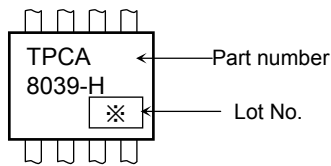
Circuit Configuration



Thermal Characteristics

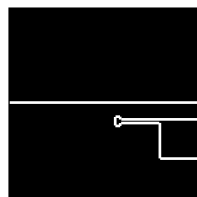
| Characteristic | Symbol | Max | Unit |
|---|----------------|------|--------------------|
| Thermal resistance, channel to case ($T_c = 25^\circ\text{C}$) | $R_{th(ch-c)}$ | 2.78 | $^\circ\text{C/W}$ |
| Thermal resistance, channel to ambient ($t = 10\text{ s}$) (Note 2a) | $R_{th(ch-a)}$ | 44.6 | $^\circ\text{C/W}$ |
| Thermal resistance, channel to ambient ($t = 10\text{ s}$) (Note 2b) | $R_{th(ch-a)}$ | 78.1 | $^\circ\text{C/W}$ |

Marking (Note 5)



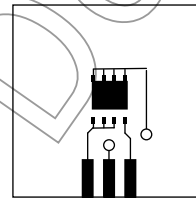
Note 1: Ensure that the channel temperature does not exceed 150°C .

Note 2: (a) Device mounted on a glass-epoxy board (a) (b) Device mounted on a glass-epoxy board (b)



(a)

FR-4
 $25.4 \times 25.4 \times 0.8$
(Unit: mm)



(b)

FR-4
 $25.4 \times 25.4 \times 0.8$
(Unit: mm)

Note 3: $V_{DD} = 24\text{ V}$, $T_{ch} = 25^\circ\text{C}$ (initial), $L = 100\ \mu\text{H}$, $R_G = 25\ \Omega$, $I_{AR} = 34\text{ A}$

Note 4: Repetitive rating: pulse width limited by maximum channel temperature

Note 5: * Weekly code: (Three digits)



Week of manufacture

(01 for the first week of the year, continuing up to 52 or 53)

Year of manufacture

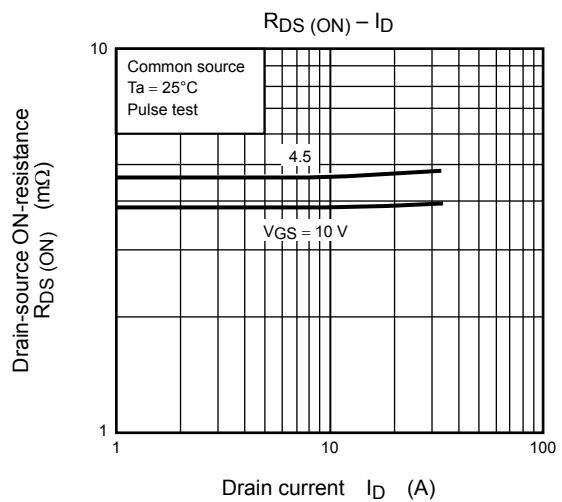
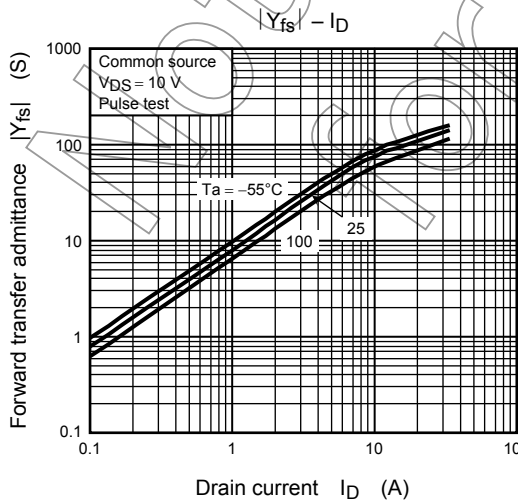
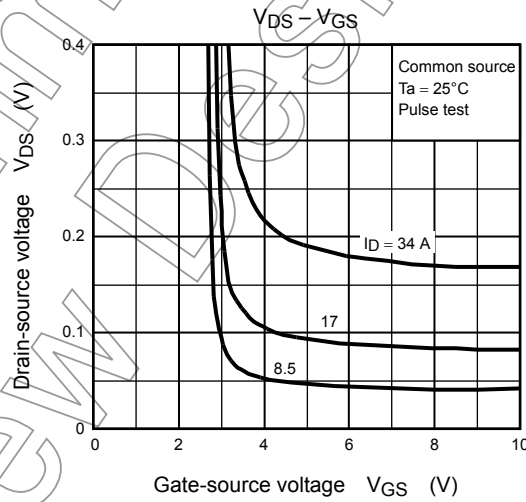
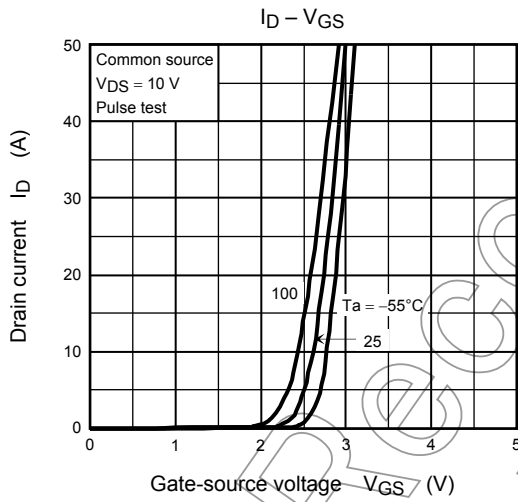
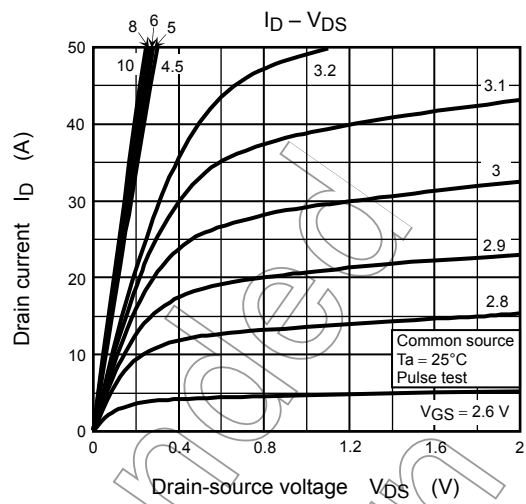
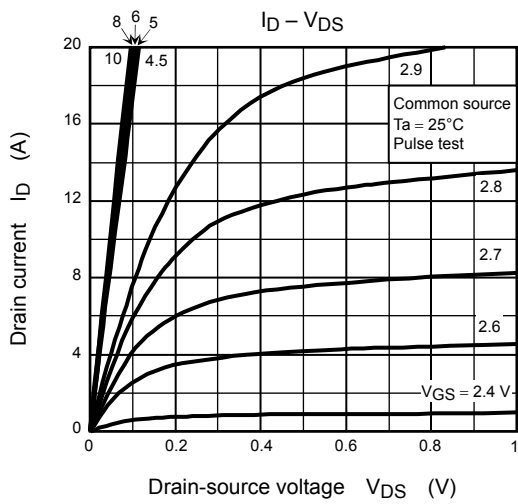
(The last digit of the year)

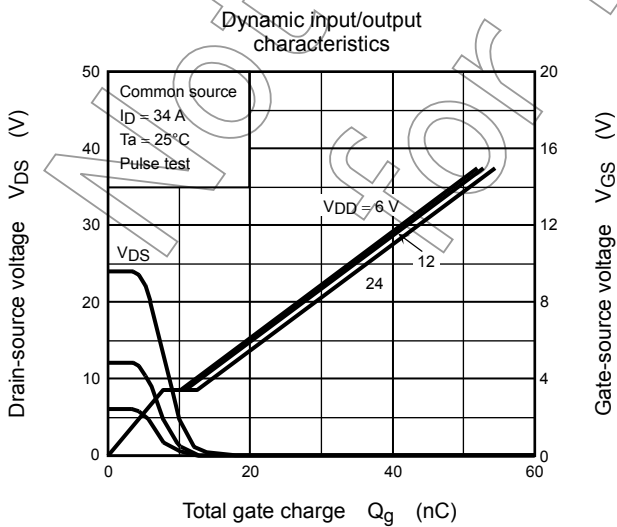
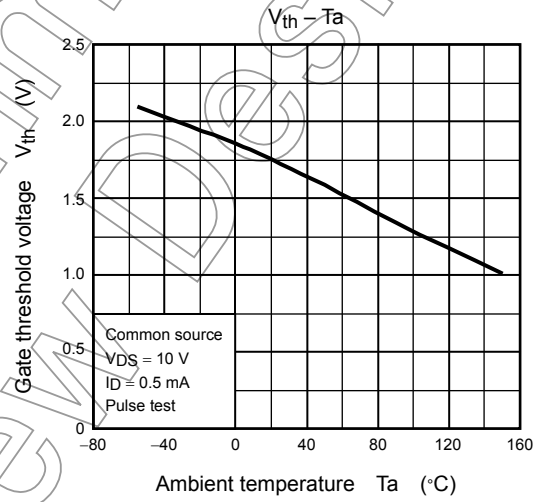
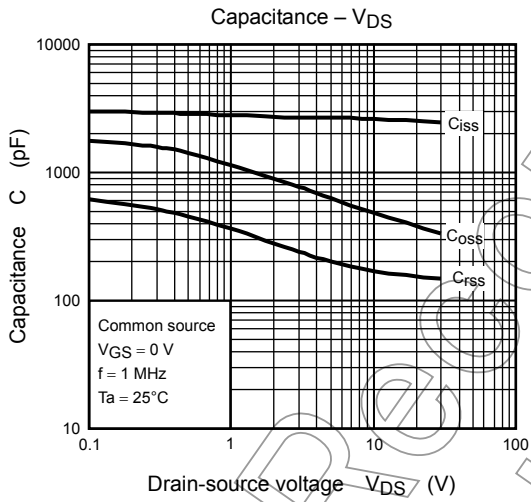
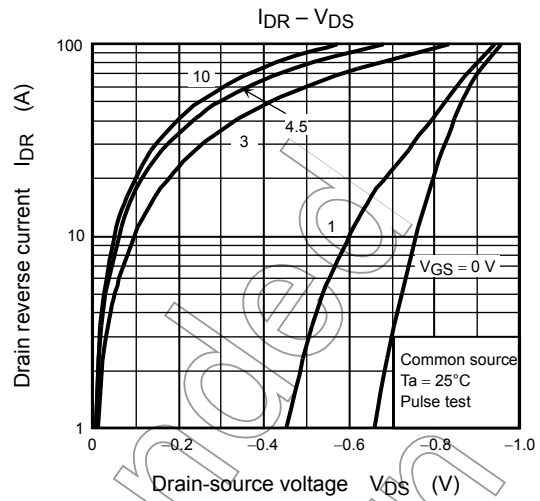
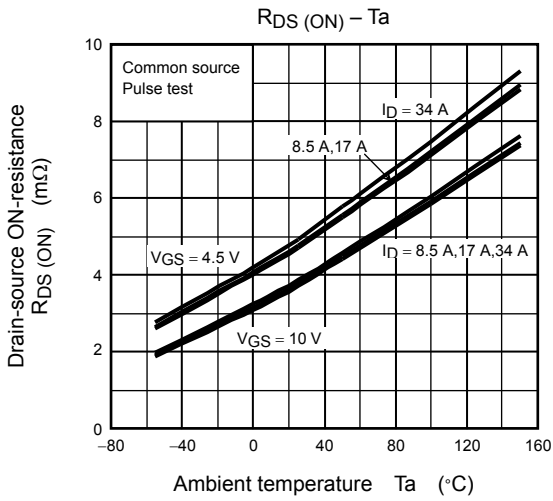
Electrical Characteristics (Ta = 25°C)

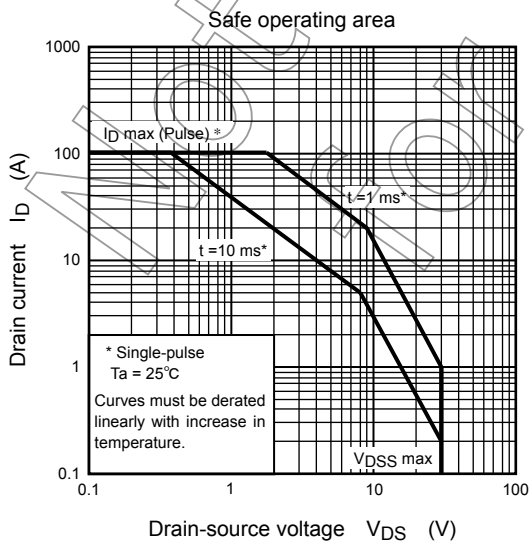
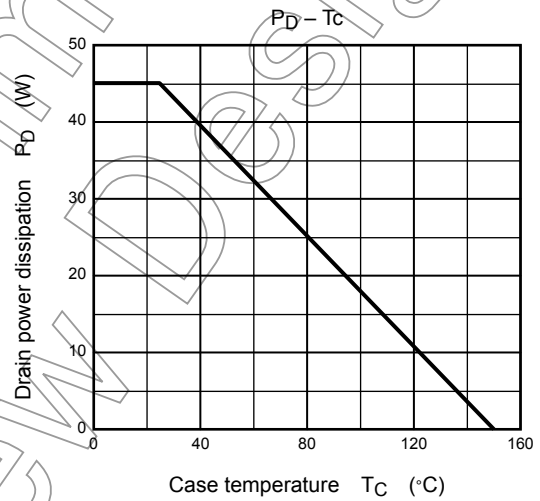
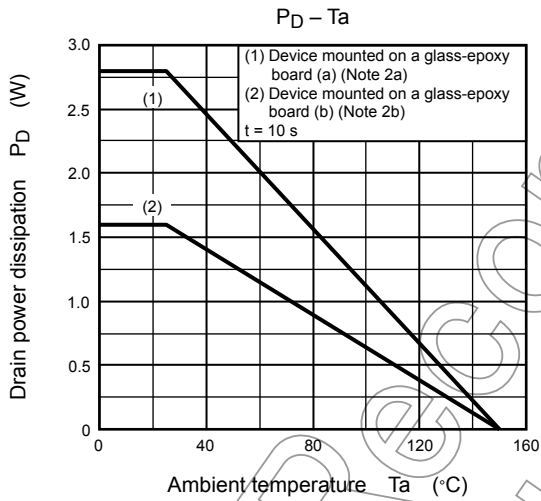
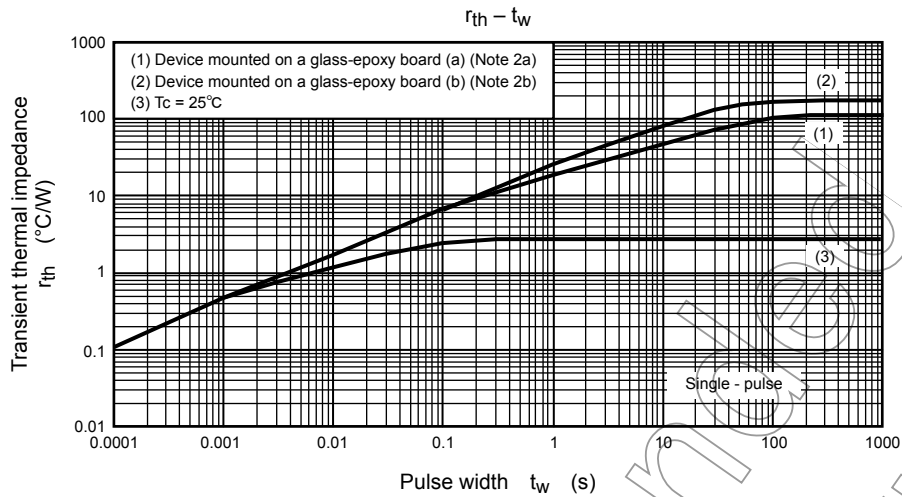
| Characteristic | | Symbol | Test Condition | Min | Typ. | Max | Unit |
|---|---------------|---------------|--|-----|------|-----------|---------------|
| Gate leakage current | | I_{GSS} | $V_{GS} = \pm 20\text{ V}, V_{DS} = 0\text{ V}$ | — | — | ± 100 | nA |
| Drain cutoff current | | I_{DSS} | $V_{DS} = 30\text{ V}, V_{GS} = 0\text{ V}$ | — | — | 10 | μA |
| Drain-source breakdown voltage | | $V_{(BR)DSS}$ | $I_D = 10\text{ mA}, V_{GS} = 0\text{ V}$ | 30 | — | — | V |
| | | $V_{(BR)DSX}$ | $I_D = 10\text{ mA}, V_{GS} = -20\text{ V}$ | 15 | — | — | |
| Gate threshold voltage | | V_{th} | $V_{DS} = 10\text{ V}, I_D = 0.5\text{ mA}$ | 1.3 | — | 2.3 | V |
| Drain-source ON-resistance | | $R_{DS(ON)}$ | $V_{GS} = 4.5\text{ V}, I_D = 17\text{ A}$ | — | 4.6 | 6.6 | m Ω |
| | | | $V_{GS} = 10\text{ V}, I_D = 17\text{ A}$ | — | 3.8 | 5.7 | |
| Forward transfer admittance | | $ Y_{fs} $ | $V_{DS} = 10\text{ V}, I_D = 17\text{ A}$ | 50 | 99 | — | S |
| Input capacitance | | C_{iss} | $V_{DS} = 10\text{ V}, V_{GS} = 0\text{ V}, f = 1\text{ MHz}$ | — | 2600 | 3400 | pF |
| Reverse transfer capacitance | | C_{rss} | | — | 170 | 270 | |
| Output capacitance | | C_{oss} | | — | 490 | — | |
| Gate resistance | | r_g | $V_{DS} = 10\text{ V}, V_{GS} = 0\text{ V}, f = 1\text{ MHz}$ | — | 1.0 | 1.5 | Ω |
| Switching time | Rise time | t_r | <p>$V_{GS} = 10\text{ V}, 0\text{ V}$ $I_D = 17\text{ A}$ $V_{DD} \approx 15\text{ V}$ $Duty \leq 1\%, t_w = 10\ \mu\text{s}$</p> | — | 3.6 | — | ns |
| | Turn-on time | t_{on} | | — | 11 | — | |
| | Fall time | t_f | | — | 7.5 | — | |
| | Turn-off time | t_{off} | | — | 41 | — | |
| Total gate charge (gate-source plus gate-drain) | | Q_g | $V_{DD} \approx 24\text{ V}, V_{GS} \approx 10\text{ V}, I_D = 34\text{ A}$ | — | 36 | — | nC |
| | | | $V_{DD} \approx 24\text{ V}, V_{GS} = 5\text{ V}, I_D = 34\text{ A}$ | — | 19 | — | |
| Gate-source charge 1 | | Q_{gs1} | | — | 7.8 | — | |
| Gate-drain ("Miller") charge | | Q_{gd} | $V_{DD} \approx 24\text{ V}, V_{GS} = 10\text{ V}, I_D = 34\text{ A}$ | — | 4.8 | — | |
| Gate switch charge | | Q_{sw} | | — | 8.6 | — | |

Source-Drain Ratings and Characteristics (Ta = 25°C)

| Characteristic | | Symbol | Test Condition | Min | Typ. | Max | Unit |
|-------------------------|----------------|-----------|---|-----|------|------|------|
| Drain reverse current | Pulse (Note 1) | I_{DRP} | — | — | — | 102 | A |
| Forward voltage (diode) | | V_{DSF} | $I_{DR} = 34\text{ A}, V_{GS} = 0\text{ V}$ | — | — | -1.2 | V |







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